**Product data sheet** 

## 1. General description

Dual common cathode power Schottky diode in TO263 (D2PAK) plastic package.





## 2. Features and benefits

- High junction temperature up to 175 °C
- Low forward voltage drop, negligible switching losses
- High efficiency

## 3. Applications

- DC to DC converters
- Freewheeling diode
- OR-ing diode
- Switched mode power supply rectifier

## 4. Quick reference data

### Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes		Values		Unit		
Absolute	Absolute maximum rating								
$V_{RRM}$	repetitive peak reverse voltage				200		V		
$I_{F(AV)}$	average forward current	$δ$ = 0.5 ; square-wave pulse; $T_{mb}$ ≤ 156 °C; per diode; Fig. 1; Fig. 2; Fig. 3		10			Α		
$I_{O(AV)}$	average output current	$\delta$ = 0.5 ; square-wave pulse; $T_{mb} \le 155$ °C; both diodes conducting		20		А			
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit		
Static characteristics									
$V_{F}$	forward voltage	$I_F = 10 \text{ A}; T_j = 25 \text{ °C}; \text{ per diode}; Fig. 6$		-	0.86	0.95	V		
I <sub>R</sub>	reverse current	$V_R = 200 \text{ V}; T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$		-	0.03	5	μA		

# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	K	cathode		A1 A2
3	A2	anode 2		— П К sym125
mb	К	mounting base; connected to cathode	1 3	sym120

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package	Orderable part number		Small packing	. •	Package deta
	name		method	quantity	version	issue date
WN3S20200CBT	TO263	WN3S20200CBTJ	Reel	800	TO263d	17-Mar-2023

# 7. Marking

### **Table 4. Marking codes**

Type number	Marking codes
WN3S20200CBT	WN3S20 200CBT

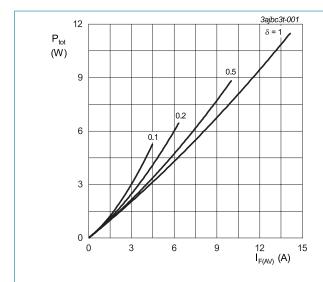
# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

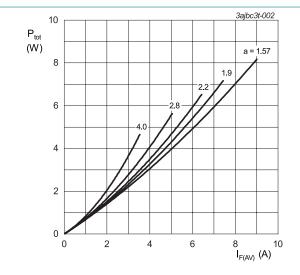
Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage			200	V
$V_{\text{RWM}}$	crest working reverse voltage			200	V
$V_R$	reverse voltage	DC		200	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 156 °C; per diode; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>		10	A
$I_{O(AV)}$	average output current	$\delta$ = 0.5; square-wave pulse; $T_{mb} \le 155$ °C; both diodes conducting		20	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4		146	А
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode		160.6	А
T <sub>stg</sub>	storage temperature			-40 to 175	°C
T <sub>j</sub>	junction temperature		[1]	-40 to 175	°C

[1] The heat generated must be less than the thermal conductivity from Junction to Ambient:  $dP_{tot}/dT_j < 1/R_{th(j-a)}$ 



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$   $V_o = 0.644 \text{ V}; R_s = 0.0119 \Omega$ 

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode



a = form factor =  $I_{F(RMS)} / I_{F(AV)}$  $V_o$  = 0.644 V;  $R_s$  = 0.0119  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

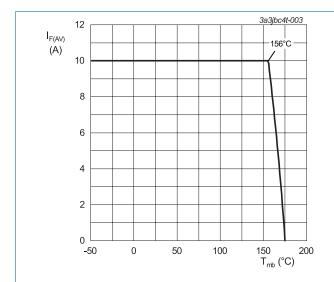


Fig. 3. Average forward current as a function of mounting base temperature; maximum values; per diode

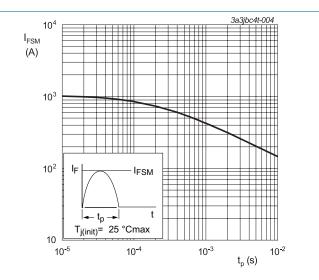


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance	per diode; Fig. 5		-	-	2.2	K/W
	from junction to mounting base	both diodes conducting		-	-	1.12	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W

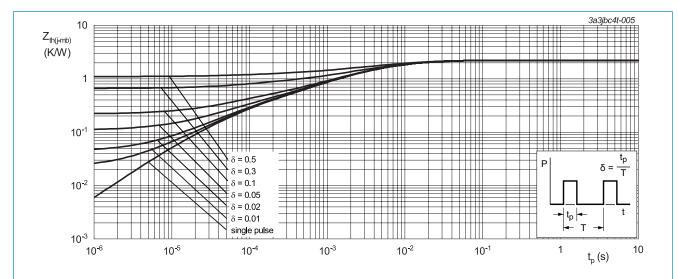
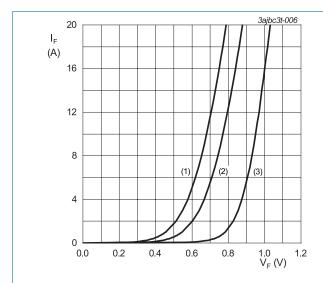


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values; per diode

## 10. Characteristics

**Table 7. Characteristics** 

$ V_F \qquad \text{forward voltage} \qquad \begin{aligned} I_F &= 10 \text{ A; } T_j = 25 \text{ °C; per diode; } \underline{Fig. 6} & - & 0.86 & 0.95 \\ I_F &= 10 \text{ A; } T_j = 125 \text{ °C; per diode} & - & 0.75 & - \\ I_F &= 10 \text{ A; } T_j = 175 \text{ °C; per diode; } \underline{Fig. 6} & - & 0.68 & 0.75 \\ I_R & \text{reverse current} & V_R &= 200 \text{ V; } T_j = 25 \text{ °C; per diode; } \underline{Fig. 7} & - & 0.03 & 5 \end{aligned} $	Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$I_{F} = 10 \text{ A; } T_{j} = 125 \text{ °C; per diode} \qquad - \qquad 0.75 \qquad - \\ I_{F} = 10 \text{ A; } T_{j} = 175 \text{ °C; per diode; } Fig. 6 \qquad - \qquad 0.68 \qquad 0.7 \\ I_{R} \qquad \text{reverse current} \qquad V_{R} = 200 \text{ V; } T_{j} = 25 \text{ °C; per diode; } Fig. 7 \qquad - \qquad 0.03 \qquad 5$	Static cha	aracteristics						
$I_F = 10 \text{ A}; T_j = 175 \text{ °C}; \text{ per diode}; \underline{\text{Fig. 6}}$ - 0.68 0.7 $I_R$ reverse current $V_R = 200 \text{ V}; T_j = 25 \text{ °C}; \text{ per diode}; \underline{\text{Fig. 7}}$ - 0.03 5	V <sub>F</sub> forward voltage		I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 6</u>		-	0.86	0.95	V
$I_R$ reverse current $V_R = 200 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; per diode; Fig. 7 - 0.03 5			I <sub>F</sub> = 10 A; T <sub>j</sub> = 125 °C; per diode		-	0.75	-	V
			I <sub>F</sub> = 10 A; T <sub>j</sub> = 175 °C; per diode; <u>Fig. 6</u>		-	0.68	0.77	V
$V_p = 200 \text{ V: T} = 125 ^{\circ}\text{C: per diode: Fig. 7}$ - 0.1 -	I <sub>R</sub>	reverse current	$V_R = 200 \text{ V}; T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$		-	0.03	5	μA
· R = 55 · 1, · 1 · 1 = 5 · 5, poi distas, <u>· · · · · · · · · · · · · · · · · · ·</u>			V <sub>R</sub> = 200 V; T <sub>j</sub> = 125 °C; per diode; <u>Fig. 7</u>		-	0.1	-	mA



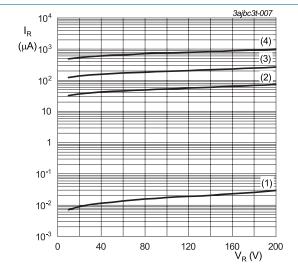
 $V_o = 0.644 \text{ V}; R_s = 0.0119 \Omega$ 

(1)  $T_j = 175$  °C; typical values

(2) T<sub>j</sub> = 175 °C; maximum values

(3)  $T_i = 25$  °C; maximum values

Fig. 6. Forward current as a function of forward voltage; per diode



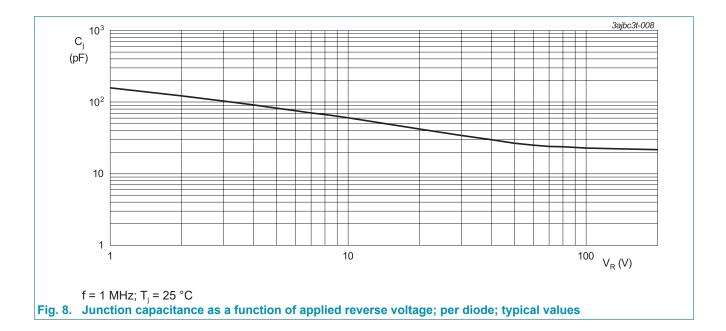
(1) T<sub>i</sub> = 25 °C; typical values

(2) T<sub>i</sub> = 125 °C; typical values

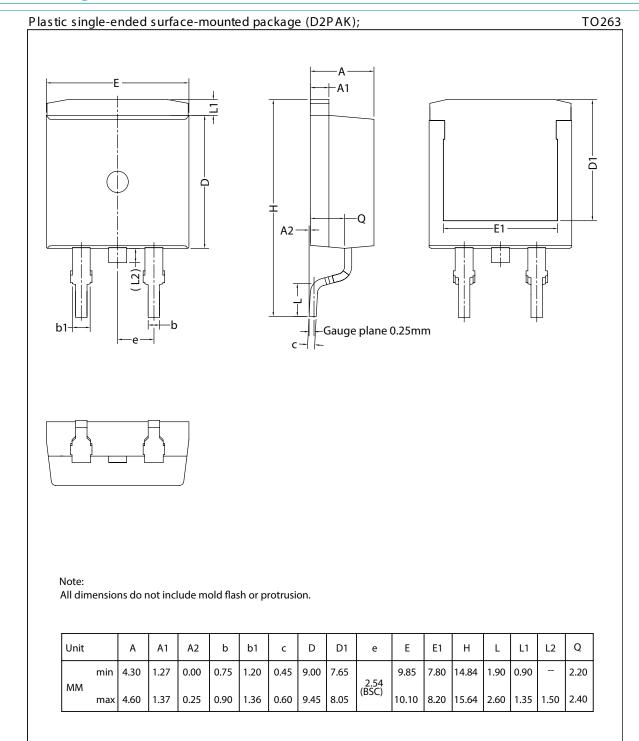
(3)  $T_i = 150$  °C; typical values

(4) T<sub>i</sub> = 175 °C; typical values

Fig. 7. Reverse leakage current as a function of reverse voltage; per diode; typical values



# 11. Package outline



## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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